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Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8347ezuajd

1 Overview

This section provides a high-level overview of the MPC8347E features. Figure 1 shows the major functional units within the MPC8347E.

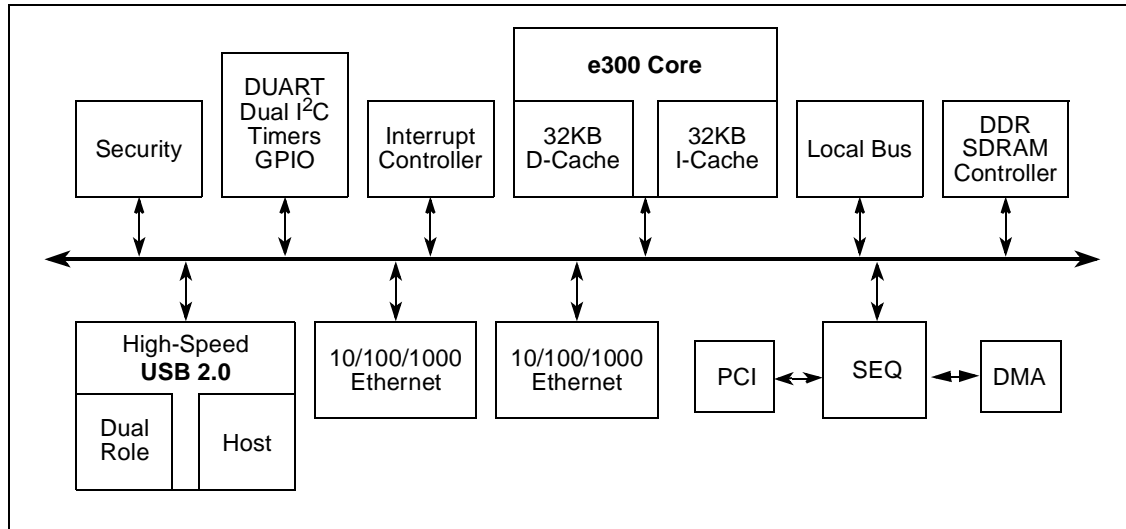


Figure 1. MPC8347E Block Diagram

Major features of the MPC8347E are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
 - High-performance, superscalar processor core
 - Floating-point, integer, load/store, system register, and branch processing units
 - 32-Kbyte instruction cache, 32-Kbyte data cache
 - Lockable portion of L1 cache
 - Dynamic power management
 - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR SDRAM memory controller
 - Programmable timing for DDR-1 SDRAM
 - 32- or 64-bit data interface, up to 333-MHz data rate for TBGA, 266 MHz for PBGA
 - Four banks of memory, each up to 1 Gbyte
 - DRAM chip configurations from 64 Mbit to 1 Gbit with x8/x16 data ports
 - Full error checking and correction (ECC) support
 - Page mode support (up to 16 simultaneous open pages)
 - Contiguous or discontiguous memory mapping
 - Read-modify-write support
 - Sleep mode for self-refresh SDRAM
 - Auto refresh

- Programmable field size up to 2048 bits
 - Elliptic curve cryptography
 - F2m and F(p) modes
 - Programmable field size up to 511 bits
- Data encryption standard (DES) execution unit (DEU)
 - DES and 3DES algorithms
 - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
 - ECB and CBC modes for both DES and 3DES
- Advanced encryption standard unit (AESU)
 - Implements the Rijndael symmetric-key cipher
 - Key lengths of 128, 192, and 256 bits
 - ECB, CBC, CCM, and counter (CTR) modes
- ARC four execution unit (AFEU)
 - Stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
- Message digest execution unit (MDEU)
 - SHA with 160- or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
- Random number generator (RNG)
- Four crypto-channels, each supporting multi-command descriptor chains
 - Static and/or dynamic assignment of crypto-execution units through an integrated controller
 - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
 - USB on-the-go mode with both device and host functionality
 - Complies with USB specification Rev. 2.0
 - Can operate as a stand-alone USB device
 - One upstream facing port
 - Six programmable USB endpoints
 - Can operate as a stand-alone USB host controller
 - USB root hub with one downstream-facing port
 - Enhanced host controller interface (EHCI) compatible
 - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
 - External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)
- Universal serial bus (USB) multi-port host controller
 - Can operate as a stand-alone USB host controller
 - USB root hub with one or two downstream-facing ports

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8347E for the 3.3-V signals, respectively.

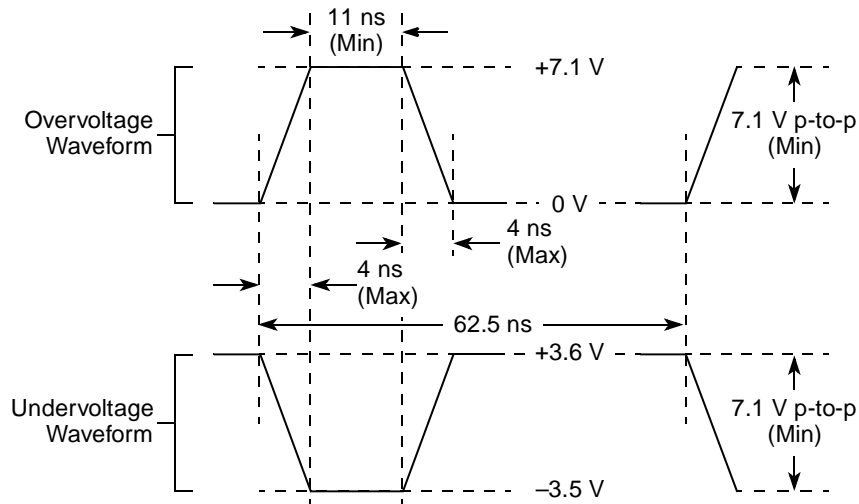


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	$OV_{DD} = 3.3\text{ V}$
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	$GV_{DD} = 2.5\text{ V}$
TSEC/10/100 signals	40	$LV_{DD} = 2.5/3.3\text{ V}$
DUART, system control, I ² C, JTAG, USB	40	$OV_{DD} = 3.3\text{ V}$
GPIO signals	40	$OV_{DD} = 3.3\text{ V}$, $LV_{DD} = 2.5/3.3\text{ V}$

2.2 Power Sequencing

MPC8347E does not require the core supply voltage and I/O supply voltages to be applied in any particular order. Note that during the power ramp up, before the power supplies are stable, there may be a period of time that I/O pins are actively driven. After the power is stable, as long as $\overline{\text{PORESET}}$ is asserted, most I/O pins are three-stated. To minimize the time that I/O pins are actively driven, it is recommended to apply core voltage before I/O voltage and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)At recommended operating conditions with GV_{DD} of $2.5\text{ V} \pm 5\%$.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKLME}	-0.9	0.3	ns	7

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, $t_{DDKL DX}$ symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
- All MCK/\overline{MCK} referenced measurements are made from the crossing of the two signals $\pm 0.1\text{ V}$.
- In the source synchronous mode, MCK/\overline{MCK} can be shifted in 1/4 applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK .
- ADDR/CMD includes all DDR SDRAM output signals except MCK/\overline{MCK} , \overline{MCS} , and $MDQ/MECC/MDM/MDQS$. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
- Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the $MCK(n)$ clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the `TIMING_CFG_2` register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the `CLK_CNTL` register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*, for a description and understanding of the timing modifications enabled by use of these bits.
- Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8347E.
- All outputs are referenced to the rising edge of $MCK(n)$ at the pins of the MPC8347E. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 5 shows the DDR SDRAM output timing for address skew with respect to any MCK .

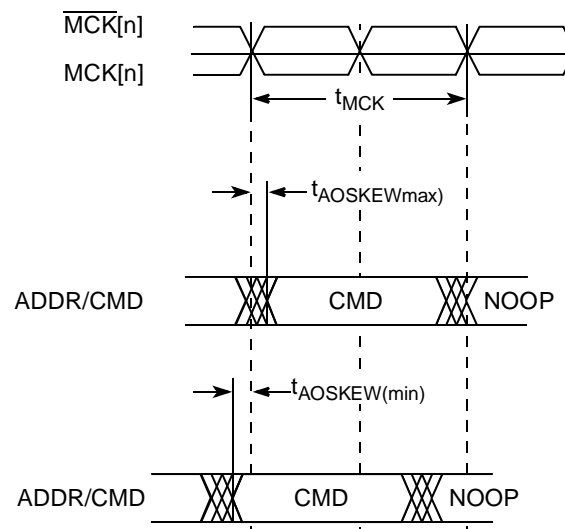
**Figure 5. Timing Diagram for t_{AOSKEW} Measurement**

Figure 6 provides the AC test load for the DDR bus.

Table 16. Expected Delays for Address/Command

Load	Delay	Unit
4 devices (12 pF)	3.0	ns
9 devices (27 pF)	3.6	ns
36 devices (108 pF) + 40 pF compensation capacitor	5.0	ns
36 devices (108 pF) + 80 pF compensation capacitor	5.2	ns

Figure 13 shows the TBI transmit AC timing diagram.

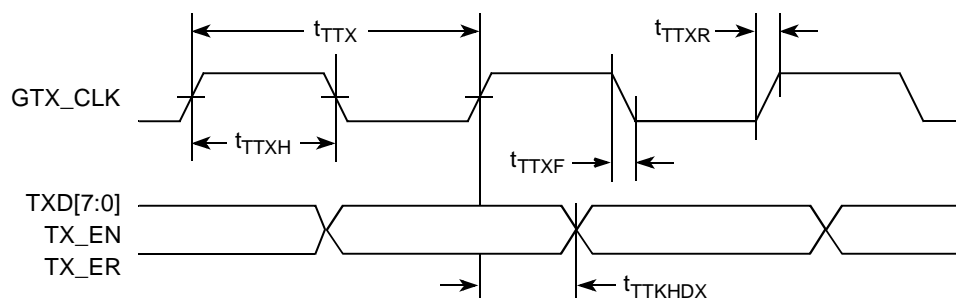


Figure 13. TBI Transmit AC Timing Diagram

8.2.3.2 TBI Receive AC Timing Specifications

Table 26 provides the TBI receive AC timing specifications.

Table 26. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
PMA_RX_CLK clock period	t_{TRX}		16.0		ns
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) setup time to rising PMA_RX_CLK	t_{TRDVKH}^2	2.5	—	—	ns
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) hold time to rising PMA_RX_CLK	t_{TRDXKH}^2	1.5	—	—	ns
RX_CLK clock rise time $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{TRXR}	0.7	—	2.4	ns
RX_CLK clock fall time $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{TRXF}	0.7	—	2.4	ns

Notes:

- The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript SK followed by the clock that is being skewed (TRX).
- Setup and hold time of even numbered RCG are measured from the rising edge of PMA_RX_CLK1. Setup and hold times of odd-numbered RCG are measured from the rising edge of PMA_RX_CLK0.

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8347E.

9.1 USB DC Electrical Characteristics

Table 31 provides the DC electrical characteristics for the USB interface.

Table 31. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
Input current	I_{IN}	—	± 5	μA
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 32 describes the general timing parameters of the USB interface of the MPC8347E.

Table 32. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol ¹	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	t_{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	2–5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

Table 35. Local Bus General Timing Parameters—DLL Bypass⁹ (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output valid	t_{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for \overline{LGTA} and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on the LALE output pin equals to the load on the LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 19 provides the AC test load for the local bus.

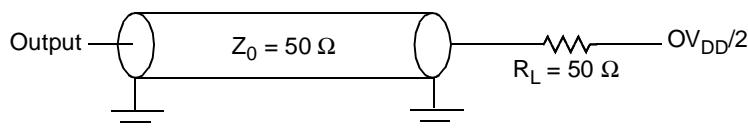


Figure 19. Local Bus C Test Load

Figure 20 through Figure 25 show the local bus signals.

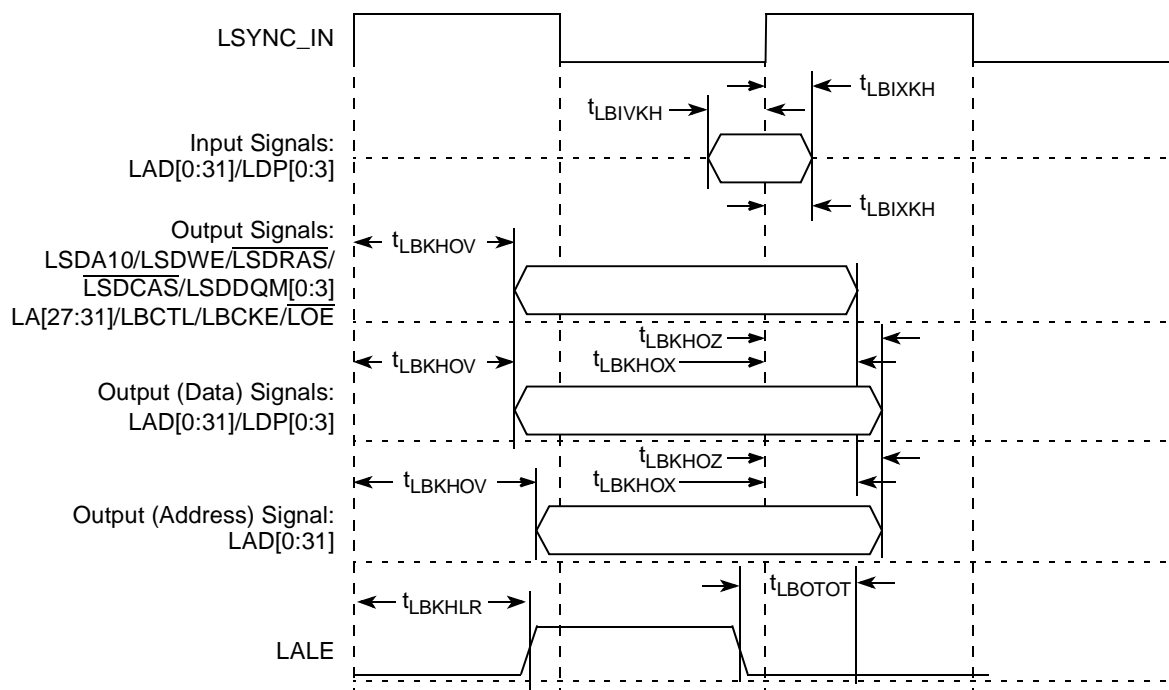


Figure 20. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

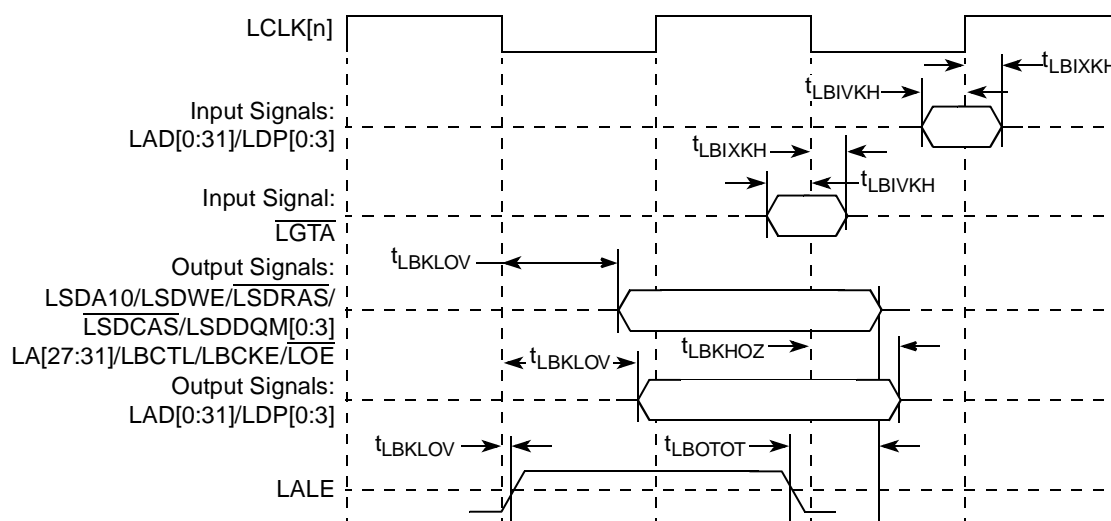


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

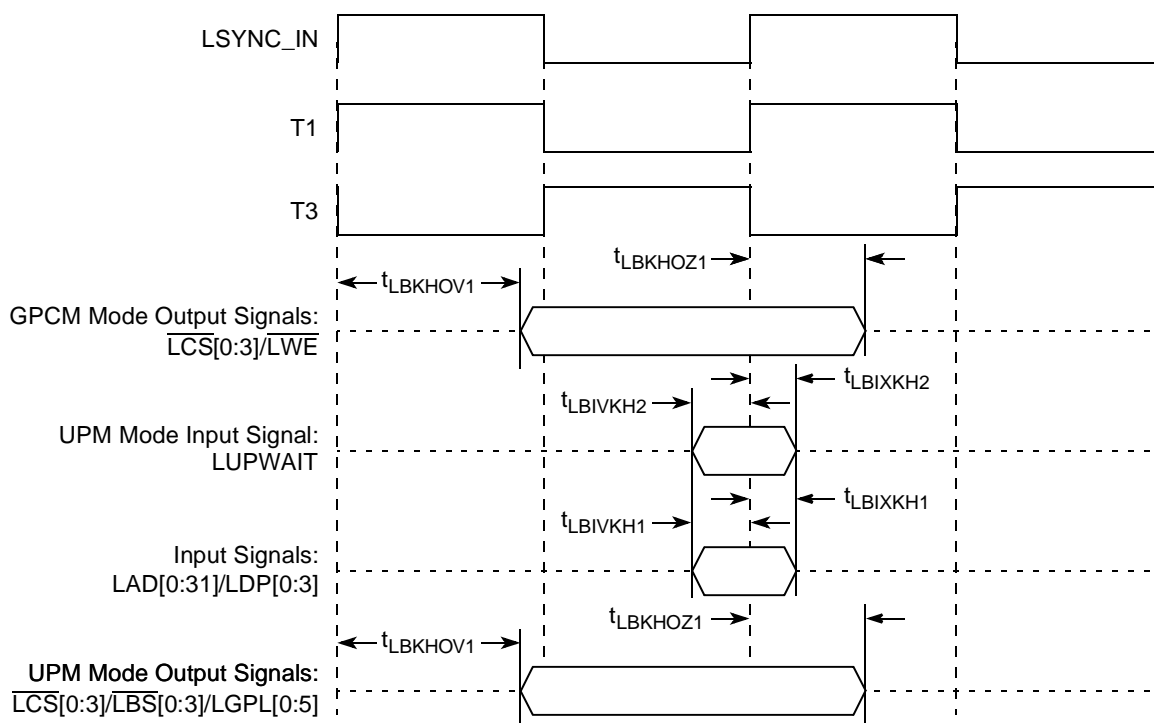


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

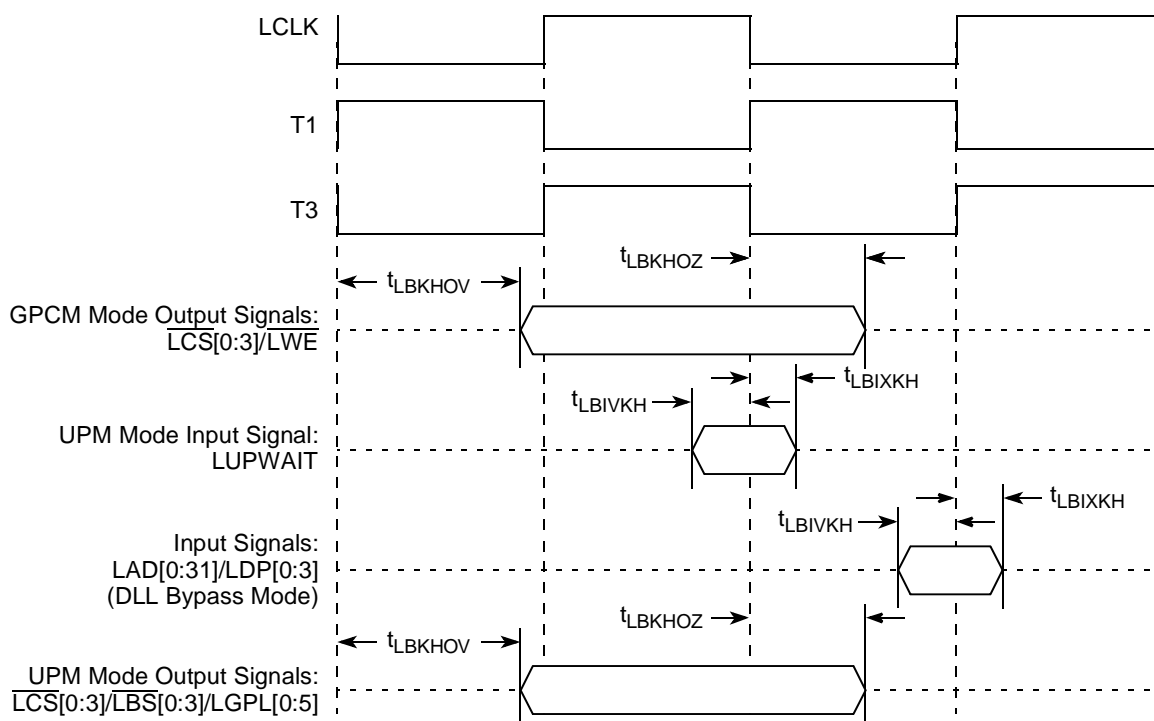


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

Figure 28 provides the $\overline{\text{TRST}}$ timing diagram.

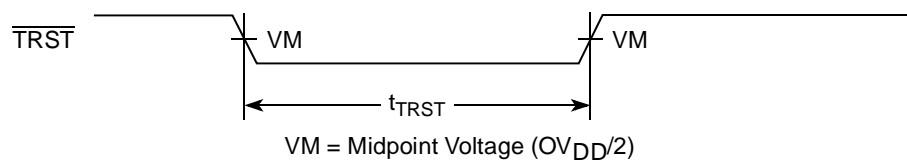


Figure 28. $\overline{\text{TRST}}$ Timing Diagram

Figure 29 provides the boundary-scan timing diagram.

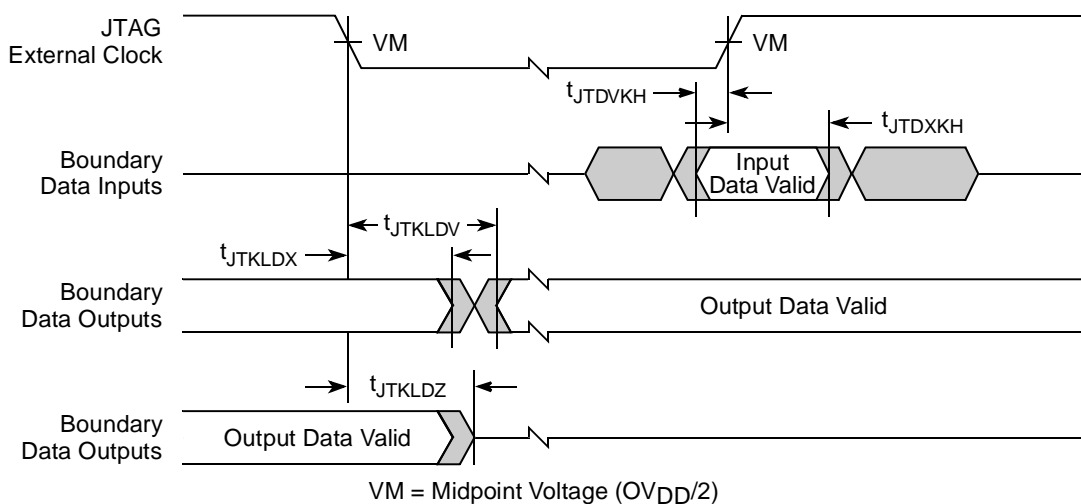


Figure 29. Boundary-Scan Timing Diagram

Figure 30 provides the test access port timing diagram.

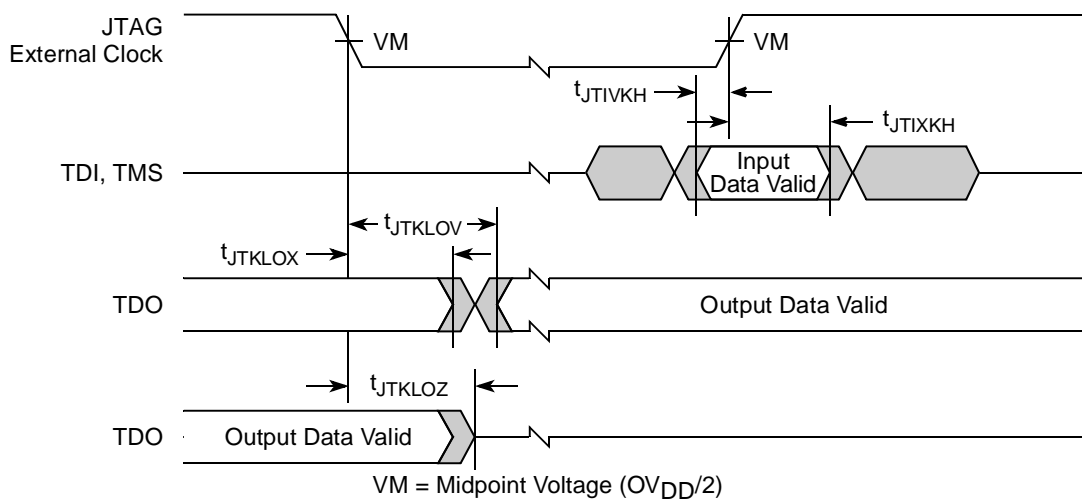


Figure 30. Test Access Port Timing Diagram

17 SPI

This section describes the SPI DC and AC electrical specifications.

17.1 SPI DC Electrical Characteristics

Table 49 provides the SPI DC electrical characteristics.

Table 49. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}		2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}		-0.3	0.8	V
Input current	I_{IN}			± 5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

17.2 SPI AC Timing Specifications

Table 50 provides the SPI input and output AC timing specifications.

Table 50. SPI AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
SPI outputs valid—Master mode (internal clock) delay	t_{NIKHOV}		6	ns
SPI outputs hold—Master mode (internal clock) delay	t_{NIKHOX}	0.5		ns
SPI outputs valid—Slave mode (external clock) delay	t_{NEKHOV}		8	ns
SPI outputs hold—Slave mode (external clock) delay	t_{NEKHOX}	2		ns
SPI inputs—Master mode (internal clock input setup time)	t_{NIIVKH}	4		ns
SPI inputs—Master mode (internal clock input hold time)	t_{NIIXKH}	0		ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4		ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2		ns

Notes:

- Output specifications are measured from the 50 percent level of the rising edge of CLKIN to the 50 percent level of the signal. Timings are measured at the pin.
- The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).

18.5 Pinout Listings

Table 51 provides the pinout listing for the MPC8347E, 672 TBGA package.

Table 51. MPC8347E (TBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
PCI_INTA/IRQ_OUT	B34	O	OV _{DD}	2
PCI_RESET_OUT	C33	O	OV _{DD}	
PCI_AD[31:0]	G30, G32, G34, H31, H32, H33, H34, J29, J32, J33, L30, K31, K33, K34, L33, L34, P34, R29, R30, R33, R34, T31, T32, T33, U31, U34, V31, V32, V33, V34, W33, W34	I/O	OV _{DD}	
PCI_C/BE[3:0]	J30, M31, P33, T34	I/O	OV _{DD}	
PCI_PAR	P32	I/O	OV _{DD}	
PCI_FRAME	M32	I/O	OV _{DD}	5
PCI_TRDY	N29	I/O	OV _{DD}	5
PCI_IRDY	M34	I/O	OV _{DD}	5
PCI_STOP	N31	I/O	OV _{DD}	5
PCI_DEVSEL	N30	I/O	OV _{DD}	5
PCI_IDSEL	J31	I	OV _{DD}	
PCI_SERR	N34	I/O	OV _{DD}	5
PCI_PERR	N33	I/O	OV _{DD}	5
PCI_REQ[0]	D32	I/O	OV _{DD}	
PCI_REQ[1]/CPCI1_HS_ES	D34	I	OV _{DD}	
PCI_REQ[2:4]	E34, F32, G29	I	OV _{DD}	
PCI_GNT0	C34	I/O	OV _{DD}	
PCI_GNT1/CPCI1_HS_LED	D33	O	OV _{DD}	
PCI_GNT2/CPCI1_HS_ENUM	E33	O	OV _{DD}	
PCI_GNT[3:4]	F31, F33	O	OV _{DD}	
M66EN	A19	I	OV _{DD}	
DDR SDRAM Memory Interface				
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV _{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
General Purpose I/O Timers				
GPIO1[0]/GTM1_TIN1/GTM2_TIN2	D27	I/O	OV _{DD}	
GPIO1[1]/GTM1_TGATE1/GTM2_TGATE2	E26	I/O	OV _{DD}	
GPIO1[2]/GTM1_TOUT1	D28	I/O	OV _{DD}	
GPIO1[3]/GTM1_TIN2/GTM2_TIN1	G25	I/O	OV _{DD}	
GPIO1[4]/GTM1_TGATE2/GTM2_TGATE1	J24	I/O	OV _{DD}	
GPIO1[5]/GTM1_TOUT2/GTM2_TOUT1	F26	I/O	OV _{DD}	
GPIO1[6]/GTM1_TIN3/GTM2_TIN4	E27	I/O	OV _{DD}	
GPIO1[7]/GTM1_TGATE3/GTM2_TGATE4	E28	I/O	OV _{DD}	
GPIO1[8]/GTM1_TOUT3	H25	I/O	OV _{DD}	
GPIO1[9]/GTM1_TIN4/GTM2_TIN3	F27	I/O	OV _{DD}	
GPIO1[10]/GTM1_TGATE4/GTM2_TGATE3	K24	I/O	OV _{DD}	
GPIO1[11]/GTM1_TOUT4/GTM2_TOUT3	G26	I/O	OV _{DD}	
USB Port 1				
MPH1_D0_ENABLEN/DR_D0_ENABLEN	C28	I/O	OV _{DD}	
MPH1_D1_SER_TXD/DR_D1_SER_TXD	F25	I/O	OV _{DD}	
MPH1_D2_VMO_SE0/DR_D2_VMO_SE0	B28	I/O	OV _{DD}	
MPH1_D3_SPEED/DR_D3_SPEED	C27	I/O	OV _{DD}	
MPH1_D4_DP/DR_D4_DP	D26	I/O	OV _{DD}	
MPH1_D5_DM/DR_D5_DM	E25	I/O	OV _{DD}	
MPH1_D6_SER_RCV/DR_D6_SER_RCV	C26	I/O	OV _{DD}	
MPH1_D7_DRVVBUS/DR_D7_DRVVBUS	D25	I/O	OV _{DD}	
MPH1_NXT/DR_SESS_VLD_NXT	B26	I	OV _{DD}	
MPH1_DIR_DPPULLUP/ DR_XCVR_SEL_DPPULLUP	E24	I/O	OV _{DD}	
MPH1_STP_SUSPEND/ DR_STP_SUSPEND	A27	O	OV _{DD}	
MPH1_PWRFAULT/ DR_RX_ERROR_PWRFAULT	C25	I	OV _{DD}	
MPH1_PCTL0/DR_TX_VALID_PCTL0	A26	O	OV _{DD}	
MPH1_PCTL1/DR_TX_VALIDH_PCTL1	B25	O	OV _{DD}	
MPH1_CLK/DR_CLK	A25	I	OV _{DD}	
USB Port 0				
MPH0_D0_ENABLEN/DR_D8_CHGVBUS	D24	I/O	OV _{DD}	
MPH0_D1_SER_TXD/DR_D9_DCHGVBUS	C24	I/O	OV _{DD}	

Table 54 provides the operating frequencies for the MPC8347E TBGA under recommended operating conditions (see Table 2).

Table 54. Operating Frequencies for TBGA

Characteristic ¹	400 MHz	533 MHz	667 MHz	Unit
e300 core frequency (<i>core_clk</i>)	266–400	266–533	266–667	MHz
Coherent system bus frequency (<i>csb_clk</i>)	100–266	100–266	100–333	MHz
DDR and memory bus frequency (MCLK) ²	100–133	100–133	100–166.67	MHz
Local bus frequency (LCLK _n) ³	16.67–133	16.67–133	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66	25–66	25–66	MHz
Security core maximum internal operating frequency	133	133	166	MHz
USB_DR, USB_MPH maximum internal operating frequency	133	133	166	MHz

¹ The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

² The DDR data rate is 2x the DDR memory bus frequency.

³ The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

Table 55 provides the operating frequencies for the MPC8347E PBGA under recommended operating conditions.

Table 55. Operating Frequencies for PBGA

Characteristic ¹	266 MHz	333 MHz	400 MHz	Unit
e300 core frequency (<i>core_clk</i>)	200–266	200–333	200–400	MHz
Coherent system bus frequency (<i>csb_clk</i>)	100–266			MHz
Local bus frequency (LCLK _n) ²	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66			MHz
Security core maximum internal operating frequency	133			MHz
USB_DR, USB_MPH maximum internal operating frequency	133			MHz

¹ The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

² The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

Table 57. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset ¹	SPMF	csb_clk : Input Clock Ratio ²	Input Clock Frequency (MHz) ²					
			16.67	25	33.33	66.67		
			csb_clk Frequency (MHz)					
Low	0010	2 : 1				133		
Low	0011	3 : 1				100	200	
Low	0100	4 : 1				100	133	266
Low	0101	5 : 1				125	166	333
Low	0110	6 : 1	100	150	200			
Low	0111	7 : 1	116	175	233			
Low	1000	8 : 1	133	200	266			
Low	1001	9 : 1	150	225	300			
Low	1010	10 : 1	166	250	333			
Low	1011	11 : 1	183	275				
Low	1100	12 : 1	200	300				
Low	1101	13 : 1	216	325				
Low	1110	14 : 1	233					
Low	1111	15 : 1	250					
Low	0000	16 : 1	266					
High	0010	2 : 1					133	
High	0011	3 : 1					100	200
High	0100	4 : 1					133	266
High	0101	5 : 1					166	333
High	0110	6 : 1					200	
High	0111	7 : 1					233	
High	1000	8 : 1						

¹ CFG_CLKIN_DIV selects the ratio between CLKIN and PCI_SYNC_OUT.

² CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.
DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

Table 60. Suggested PLL Configurations

Ref No. ¹	RCWL		400 MHz Device			533 MHz Device			667 MHz Device		
	SPMF	CORE PLL	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)
33 MHz CLKIN/PCI_CLK Options											
922	1001	0100010	—	—	—	—	—	f300	33	300	300
723	0111	0100011	33	233	350	33	233	350	33	233	350
604	0110	0000100	33	200	400	33	200	400	33	200	400
624	0110	0100100	33	200	400	33	200	400	33	200	400
803	1000	0000011	33	266	400	33	266	400	33	266	400
823	1000	0100011	33	266	400	33	266	400	33	266	400
903	1001	0000011	—			33	300	450	33	300	450
923	1001	0100011	—			33	300	450	33	300	450
704	0111	0000011	—			33	233	466	33	233	466
724	0111	0100011	—			33	233	466	33	233	466
A03	1010	0000011	—			33	333	500	33	333	500
804	1000	0000100	—			33	266	533	33	266	533
705	0111	0000101	—			—			33	233	583
606	0110	0000110	—			—			33	200	600
904	1001	0000100	—			—			33	300	600
805	1000	0000101	—			—			33	266	667
A04	1010	0000100	—			—			33	333	667
66 MHz CLKIN/PCI_CLK Options											
304	0011	0000100	66	200	400	66	200	400	66	200	400
324	0011	0100100	66	200	400	66	200	400	66	200	400
403	0100	0000011	66	266	400	66	266	400	66	266	400
423	0100	0100011	66	266	400	66	266	400	66	266	400
305	0011	0000101	—			66	200	500	66	200	500
503	0101	0000011	—			66	333	500	66	333	500
404	0100	0000100	—			66	266	533	66	266	533
306	0011	0000110	—			—			66	200	600
405	0100	0000101	—			—			66	266	667
504	0101	0000100	—			—			66	333	667

¹ The PLL configuration reference number is the hexadecimal representation of RCWL, bits 4–15 associated with the SPMF and COREPLL settings given in the table.

² The input clock is CLKIN for PCI host mode or PCI_CLK for PCI agent mode.

required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8347E.

21.1 System Clocking

The MPC8347E includes two PLLs:

1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in [Section 19.1, “System PLL Configuration.”](#)
2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in [Section 19.2, “Core PLL Configuration.”](#)

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins (AV_{DD1} , AV_{DD2} , respectively). The AV_{DD} level should always equal to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in [Figure 42](#), one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

[Figure 42](#) shows the PLL power supply filter circuit.

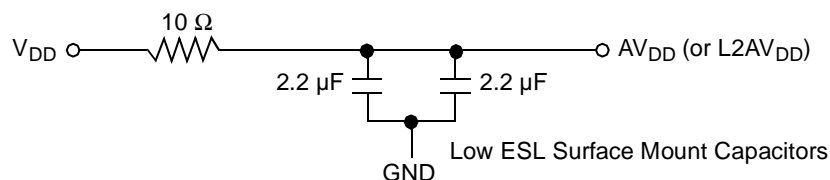


Figure 42. PLL Power Supply Filter Circuit

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8347E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8347E system, and the MPC8347E itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the MPC8347E. These capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 μF . Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 μF (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD} , GV_{DD} , or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , GV_{DD} , LV_{DD} , OV_{DD} , and GND pins of the MPC8347E.

21.5 Output Buffer DC Impedance

The MPC8347E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see [Figure 43](#)). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.